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Supporting Information

Investigation on Out-of-Plane Structural Properties of Graphene Monolayer with Gap-Plasmon :Mode-Selective Raman Enhancement and Influence of Additional SP³ type Defect

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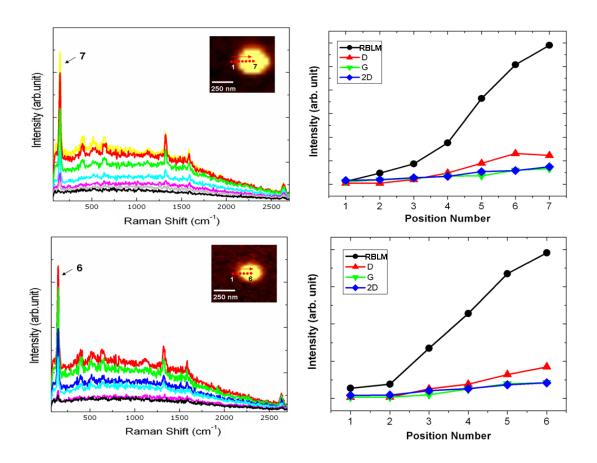


Figure S1. Two additional junctions showing similar lateral approach profiles and the resulting mode-dependent Raman enhancement.

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